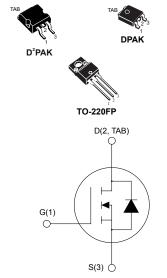


Datasheet

N-channel 650 V, 0.56 Ω typ., 7 A MDmesh M5 Power MOSFETs in a D²PAK, DPAK and TO-220FP packages



AM01475v1_noZen



Product status links
STB8N65M5
STD8N65M5
STF8N65M5

Features

Order codes	V _{DS} @ T _J max.	R _{DS(on)} max.	l _D	P _{TOT}
STB8N65M5	710 V			70 W
STD8N65M5		0.60 Ω	7 A	70 W
STF8N65M5				25 W

- Extremely low R_{DS(on)}
- · Low gate charge and input capacitance
- · Excellent switching performance
- 100% avalanche tested

Applications

· Switching applications

Description

These devices are N-channel Power MOSFETs based on the MDmesh M5 innovative vertical process technology combined with the well-known PowerMESH horizontal layout. The resulting products offer extremely low on-resistance, making them particularly suitable for applications requiring high power and superior efficiency.



1 Electrical ratings

Table 1. Absolute maximum ratings

Comple al	Symbol Parameter		Value		
Symbol	Parameter	D ² PAK	DPAK	TO-220FP	Unit
V_{GS}	Gate-source voltage	±25			V
I _D	Drain current (continuous) at T _C = 25 °C		7	7 ⁽¹⁾	А
I _D	Drain current (continuous) at T _C = 100 °C	4	4.4 4.4(1)		А
I _{DM} ⁽²⁾	Drain current (pulsed)	28		28 28 ⁽¹⁾	
P _{TOT}	Total power dissipation at T _C = 25 °C	70		25	W
dv/dt (3)	Peak diode recovery voltage slope	15		V/ns	
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s; T _C = 25 °C)			2500	V
Tj	T _j Operating junction temperature range		554.450		°C
T _{stg}	Storage temperature range	-55 to 150		C	

- 1. Limited by maximum junction temperature.
- 2. Pulse width limited by safe operating area.
- 3. $I_{SD} \le 7$ A, $di/dt \le 400$ A/ μ s; V_{DS} (peak) $< V_{(BR)DSS}$, $V_{DD} = 400$ V.

Table 2. Thermal data

Symbol Parameter			Unit		
Symbol	r di dilletei	D ² PAK	DPAK	TO-220FP	OIIII.
R _{thJC}	Thermal resistance, junction-to-case	1.79		5	°C/W
R _{thJA}	Thermal resistance, junction-to-ambient			62.5	°C/W
R _{thJB} (1)	Thermal resistance, junction-to-board	30	50		°C/W

^{1.} When mounted on an 1-inch² FR-4, 2oz Cu board.

Table 3. Avalanche characteristics

Symbol Parameter			Unit		
Syllibol	raiametei	D ² PAK	DPAK	TO-220FP	Onit
I _{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T _J max.)	2		А	
E _{AS}	Single pulse avalanche energy (starting $T_j = 25$ °C, $I_D = I_{AR}$, $V_{DD} = 50$ V)	120		mJ	

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2 Electrical characteristics

 T_C = 25 °C unless otherwise specified.

Table 4. On/off states

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	I_D = 1 mA, V_{GS} = 0 V	650			V
less	I _{DSS} Zero gate voltage drain current	V _{GS} = 0 V, V _{DS} = 650 V			1	μA
IDSS		V _{GS} = 0 V, V _{DS} = 650 V, T _C = 125 °C ⁽¹⁾			100	μA
I _{GSS}	Gate body leakage current	V _{DS} = 0 V, V _{GS} = ±25 V			±100	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_{D} = 250 \mu A$	3	4	5	V
R _{DS(on)}	Static drain-source on-resistance	V _{GS} = 10 V, I _D = 3.5 A		0.56	0.60	Ω

^{1.} Specified by design, not tested in production.

Table 5. Dynamic

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
C _{iss}	Input capacitance			690		
C _{oss}	Output capacitance	V _{DS} = 100 V, f = 1 MHz, V _{GS} = 0 V		18		pF
C _{rss}	Reverse transfer capacitance			2		
C _{o(tr)} (1)	Equivalent output capacitance time related	V _{DS} = 0 to 520 V, V _{GS} = 0 V		17		pF
C _{o(er)} (2)	Equivalent output capacitance energy related	V _{DS} = 0 to 320 v, v _{GS} = 0 v		52		pF
R _g	Gate input resistance	f = 1 MHz open drain	2	5	8	Ω
Qg	Total gate charge	V _{DD} = 520 V, I _D = 3.5 A,		15		
Q _{gs}	Gate-source charge	V _{GS} = 0 to 10 V		3.6		nC
Q _{gd}	Gate-drain charge	(see Figure 18. Test circuit for gate charge behavior)		6		

C_{O(tr)} is an equivalent capacitance that provides the same charging time as Coss while V_{DS} is rising from 0 V to the stated value.

Table 6. Switching times

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
t _{d(off)}	Turn-off delay time	V _{DD} = 400 V, I _D = 4 A,	-	50	-	
t _{r(v)}	Voltage rise time	$R_G = 4.7 \Omega$, $V_{GS} = 10 V$	-	14	-	
t _{c(off)}	Crossing time off	(see Figure 19. Test circuit for inductive load switching and diode recovery times		20	-	ns
t _{f(i)}	Current fall time	and Figure 22. Switching time waveform)	-	11	-	

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^{2.} $C_{o(er)}$ is an equivalent capacitance that provides the same stored energy as C_{oss} while V_{DS} is rising from 0 V to the stated value.



Table 7. Source-drain diode

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
I _{SD}	Source-drain current		-		7	Α
I _{SDM} ⁽¹⁾	Source-drain current (pulsed)		-		28	A
V _{SD} ⁽²⁾	Forward on voltage	I _{SD} = 7 A, V _{GS} = 0 V	-		1.5	V
t _{rr}	Reverse recovery time	I _{SD} = 7 A, di/dt = 100 A/μs	-	200		ns
Q _{rr}	Reverse recovery charge	V _{DD} = 100 V (see Figure 19. Test circuit for inductive load switching and diode recovery times)		1.6		μC
I _{RRM}	Reverse recovery current			16		Α
t _{rr}	Reverse recovery time	I _{SD} = 7 A, di/dt = 100 A/μs	-	263		ns
Q _{rr}	Reverse recovery charge	V _{DD} = 100 V, T _J = 150 °C		1.9		μC
I _{RRM}	Reverse recovery current	(see Figure 19. Test circuit for inductive load switching and diode recovery times)	-	15		Α

^{1.} Pulse width limited by safe operating area.

^{2.} Pulsed: pulse duration = $300 \mu s$, duty cycle 1.5%.



2.1 Electrical characteristics (curves)

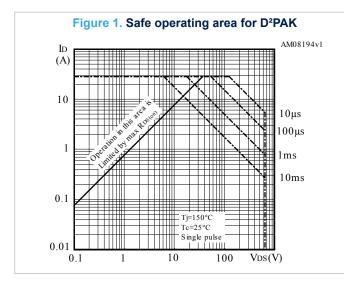
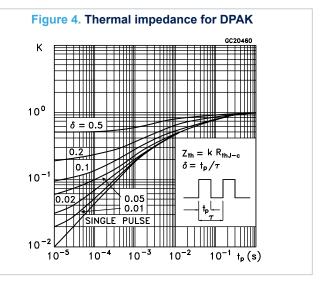
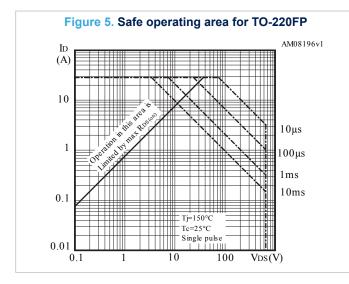
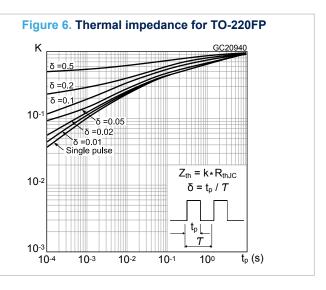


Figure 2. Thermal impedance for D²PAK 0.2 10^{-1} 0.05 $Z_{th} = k * R_{thJC}$ $\delta = t_p / T$ 0.01 SINGLE PULSE t_p| 10 10^{-5} 10^{-4} 10^{-3} 10^{-2} 10^{-1} $t_p(s)$







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Figure 7. Output characterisics AM08197v1 ID(A) $V_{GS}=10V$ 12 7.5V 10 6.5V 8 6 6V 4 2 5.5V 5 10 15 VDS(V)

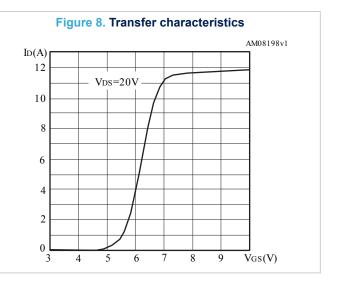
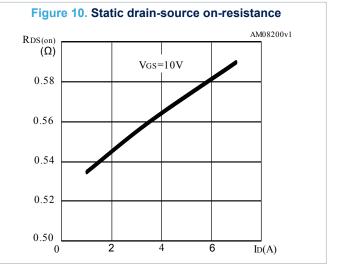
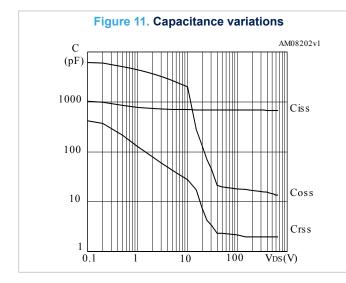
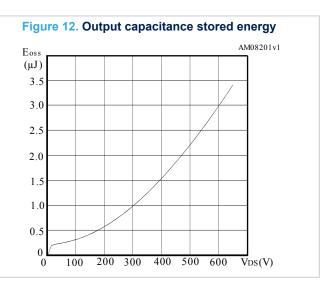


Figure 9. Gate charge vs gate-source voltage AM03195v1 VDS (V) Vgs (V) VDD=520V Vgs Vds 12 $I_D=3.5A$ 500 10 -400 8 300 6 200 4 100 2 0 10 15 Qg(nC)







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Figure 13. Normalized gate threshold voltage vs temperature

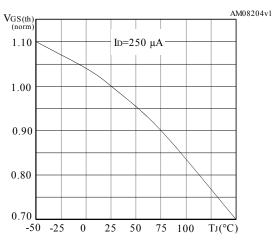


Figure 14. Normalized on-resistance vs temperature

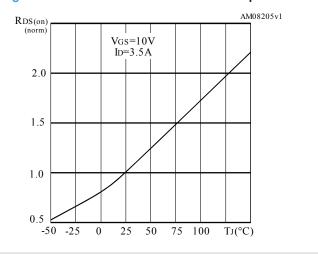


Figure 15. Switching energy vs gate resistance

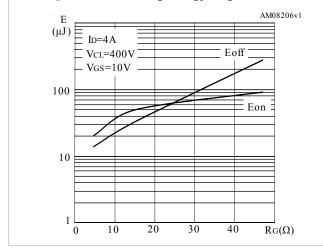
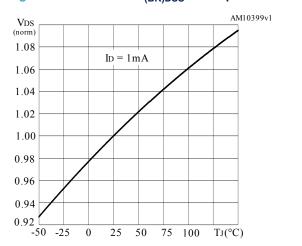


Figure 16. Normalized V_{(BR)DSS} vs temperature



Note: E_{on} including reverse recovery of a SiC diode.

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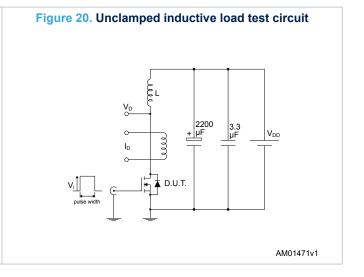


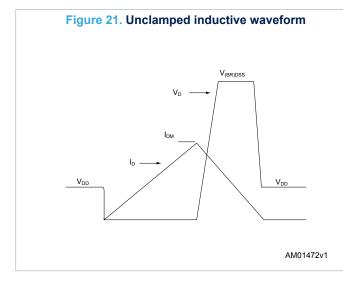
3 Test circuits

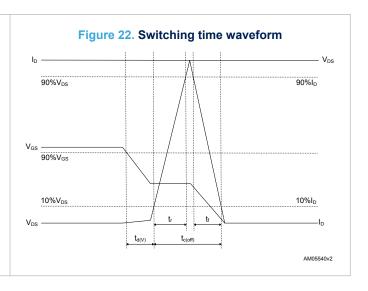
Figure 17. Test circuit for resistive load switching times

AM01468v1

AM01470v1







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4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 D²PAK (TO-263) type A package information

E E/2

B1

SEATING PLANE

COPLANARITY A1

0.25

Figure 23. D²PAK (TO-263) type A package outline

0079457_26

GAUGE PLANE



Table 8. D²PAK (TO-263) type A package mechanical data

Div		mm	
Dim.	Min.	Тур.	Max.
Α	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
С	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10.00		10.40
E1	8.30	8.50	8.70
E2	6.85	7.05	7.25
е		2.54	
e1	4.88		5.28
Н	15.00		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.40	
V2	0°		8°

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9.75 16.90 1.60 2.54 5.08

Figure 24. D²PAK (TO-263) recommended footprint (dimensions are in mm)

0079457_Rev26_footprint



4.2 DPAK (TO-252) type A package information

Ε THERMAL PAD c2 *b4* - E1 -*L2* D1 D <u>L4</u> <u>b(2x)</u> R С SEATING PLANE <u>A</u>2 (L1)*V2* 0,25

Figure 25. DPAK (TO-252) type A package outline

0068772_A_30



Table 9. DPAK (TO-252) type A mechanical data

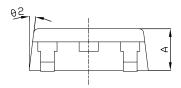
Dim.	mm					
Dim.	Min.	Тур.	Max.			
А	2.20		2.40			
A1	0.90		1.10			
A2	0.03		0.23			
b	0.64		0.90			
b4	5.20		5.40			
С	0.45		0.60			
c2	0.48		0.60			
D	6.00		6.20			
D1	4.95	5.10	5.25			
Е	6.40		6.60			
E1	4.60	4.70	4.80			
е	2.159	2.286	2.413			
e1	4.445	4.572	4.699			
Н	9.35		10.10			
L	1.00		1.50			
(L1)	2.60	2.80	3.00			
L2	0.65	0.80	0.95			
L4	0.60		1.00			
R		0.20				
V2	0°		8°			

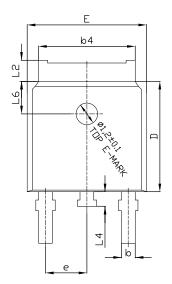
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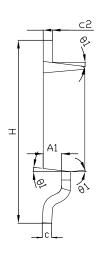


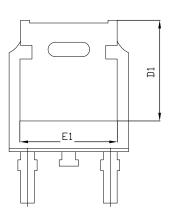
4.3 DPAK (TO-252) type C package information

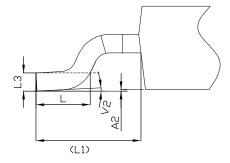
Figure 26. DPAK (TO-252) type C package outline











0068772_C_30

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Downloaded from Arrow.com.



Table 10. DPAK (TO-252) type C mechanical data

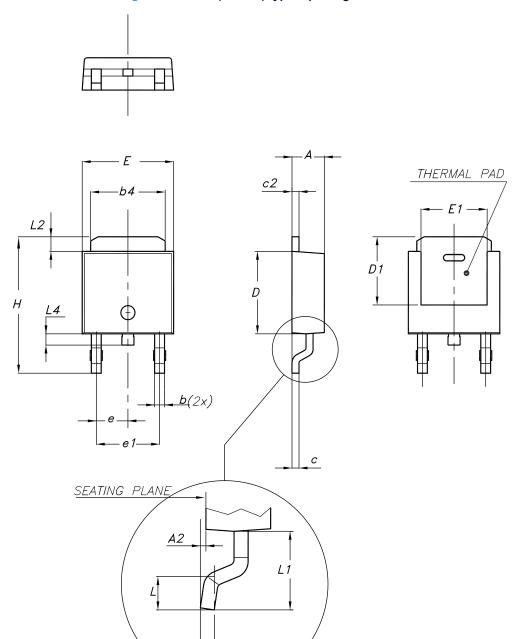
Div		mm				
Dim.	Min.	Тур.	Max.			
А	2.20	2.30	2.38			
A1	0.90	1.01	1.10			
A2	0.00		0.10			
b	0.72		0.85			
b4	5.13	5.33	5.46			
С	0.47		0.60			
c2	0.47		0.60			
D	6.00	6.10	6.20			
D1	5.25					
Е	6.50	6.60	6.70			
E1	4.70					
е	2.186	2.286	2.386			
Н	9.80	10.10	10.40			
L	1.40	1.50	1.70			
L1		2.90 REF				
L2	0.90		1.25			
L3		0.51 BSC				
L4	0.60	0.80	1.00			
L6		1.80 BSC				
θ1	5°	7°	9°			
θ2	5°	7°	9°			
V2	0°		8°			

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4.4 DPAK (TO-252) type E package information

Figure 27. DPAK (TO-252) type E package outline



GAUGE PLANE

0.508

0068772_typeE_rev.30



Table 11. DPAK (TO-252) type E mechanical data

Dim.	mm				
	Min.	Тур.	Max.		
А	2.18		2.39		
A2			0.13		
b	0.65		0.884		
b4	4.95		5.46		
С	0.46		0.61		
c2	0.46		0.60		
D	5.97		6.22		
D1	5.21				
E	6.35		6.73		
E1	4.32				
е		2.286			
e1		4.572			
Н	9.94		10.34		
L	1.50		1.78		
L1		2.74			
L2	0.89		1.27		
L4			1.02		

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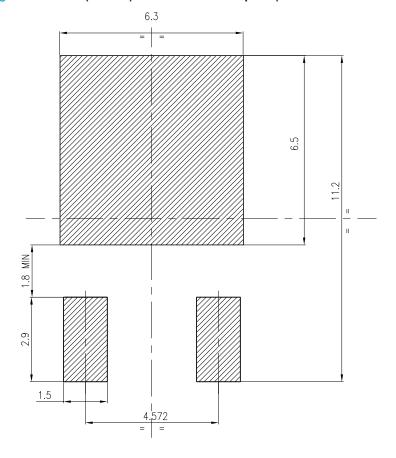


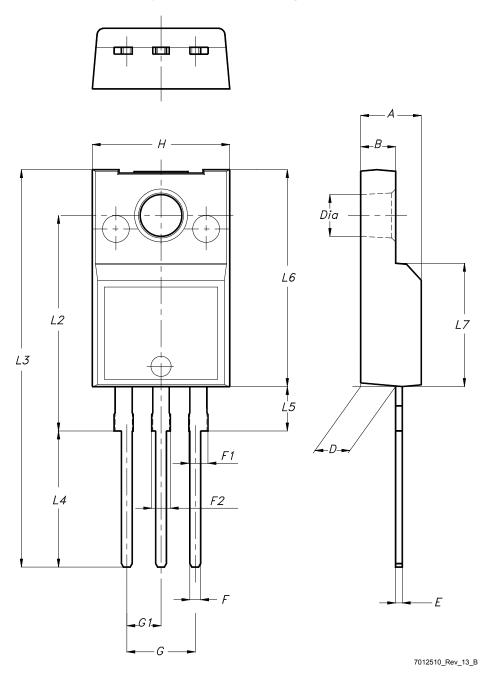
Figure 28. DPAK (TO-252) recommended footprint (dimensions are in mm)

FP_0068772_30



4.5 TO-220FP package information

Figure 29. TO-220FP package outline



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Table 12. TO-220FP package mechanical data

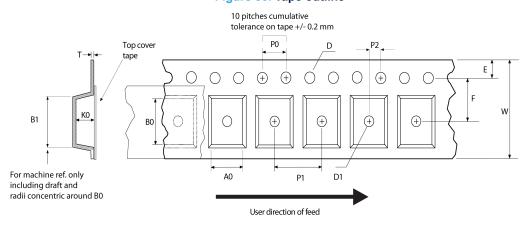
Dim.	mm				
	Min.	Тур.	Max.		
А	4.40		4.60		
В	2.50		2.70		
D	2.50		2.75		
E	0.45		0.70		
F	0.75		1.00		
F1	1.15		1.70		
F2	1.15		1.70		
G	4.95		5.20		
G1	2.40		2.70		
Н	10.00		10.40		
L2		16.00			
L3	28.60		30.60		
L4	9.80		10.60		
L5	2.90		3.60		
L6	15.90		16.40		
L7	9.00		9.30		
Dia	3.00		3.20		

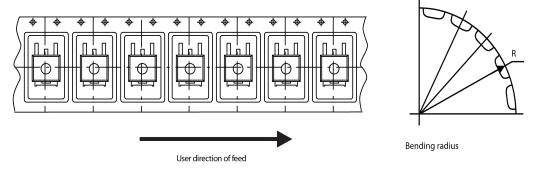
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4.6 D²PAK and DPAK packing information

Figure 30. Tape outline



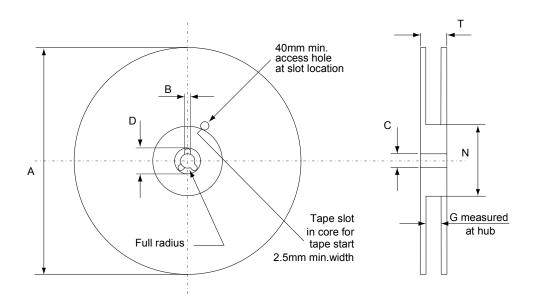


AM08852v1

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Figure 31. Reel outline



AM06038v1

Table 13. D2PAK tape and reel mechanical data

Таре		Reel			
Dim.	mm		Dim.	mm	
Dilli.	Min.	Max.	Dim.	Min.	Max.
A0	10.5	10.7	А		330
В0	15.7	15.9	В	1.5	
D	1.5	1.6	С	12.8	13.2
D1	1.59	1.61	D	20.2	
Е	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	Т		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
Т	0.25	0.35			
W	23.7	24.3			

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Table 14. DPAK tape and reel mechanical data

Таре				Reel		
Dim.	mm		Di		mm	
	Min.	Max.	Dim.	Min.	Max.	
A0	6.8	7	А		330	
В0	10.4	10.6	В	1.5		
B1		12.1	С	12.8	13.2	
D	1.5	1.6	D	20.2		
D1	1.5		G	16.4	18.4	
E	1.65	1.85	N	50		
F	7.4	7.6	Т		22.4	
K0	2.55	2.75				
P0	3.9	4.1	Base qty.		2500	
P1	7.9	8.1	Bulk qty.		2500	
P2	1.9	2.1				
R	40					
Т	0.25	0.35				
W	15.7	16.3				

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5 Ordering information

Table 15. Order codes

Order codes	Marking	Package	Packing
STB8N65M5	TD8N65M5 8N65M5	D²PAK	Tape and reel
STD8N65M5		DPAK	Tape and reel
STF8N65M5		TO-220FP	Tube

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Revision history

Table 16. Document revision history

Date	Revision	Changes
23-Oct-2009	1	First release.
14-Oct-2010	2	Document status promoted from preliminary data to datasheet.
05-Jul-2011	3	Table 7: Source drain diode has been updated.
04-Oct-2012	4	 Updated: Figure 1, 10, 14 and 17. Updated: note1 and 3 below the Table 2 Updated the entire Section 4: Package mechanical data. Updated title and description on the cover page.
29-Oct-2012	5	– Updated R _g values in <i>Table 5</i> .
03-Mar-2022	6	The part numbers STI8N65M5, STP8N65M5, STU8N65M5 have been moved to a separate datasheet and the document has been updated accordingly. Modified $R_{\rm g}$ value in Table 5. Dynamic. Updated Section 4 Package information. Minor text changes.

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	4.2	DPAK (TO-252) type A package information	12			
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5	Ord	ering information	24			
Rev	/ision	history	25			



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